

CMXSH2-4LS
SURFACE MOUNT
DUAL PAIR, IN-SERIES
LOW V_F
SILICON SCHOTTKY DIODES



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXSH2-LS consists of Dual, In-Series pairs of Low V_F Silicon Schottky Diodes, and is manufactured in a SUPERmini™ SOT-26 surface mount package. This device can be configured as a bridge rectifier using the optional mounting pad configuration on the following page.

MARKING CODE: CXS4L

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Repetitive Forward Current
 Peak Forward Surge Current, $t_p=10\text{ms}$
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL

V_{RRM} 40
 I_F 200
 I_{FRM} 350
 I_{FSM} 1.0
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
 mA
 mA
 A
 mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

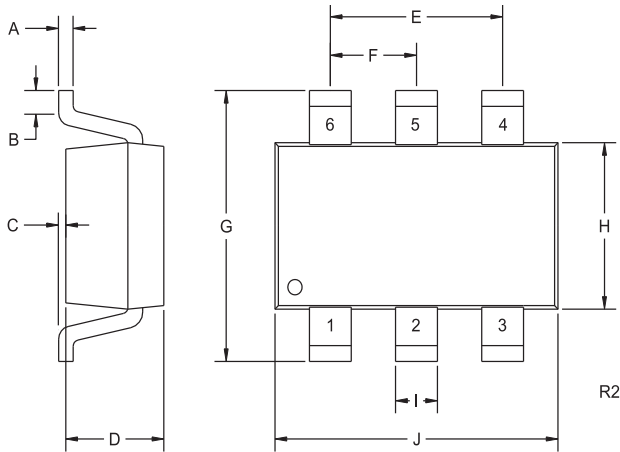
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_R	$V_R=20\text{V}$		11	50	μA
BV_R	$I_R=100\mu\text{A}$	40	53		V
V_F	$I_F=10\text{mA}$		0.24	0.325	V
V_F	$I_F=100\text{mA}$		0.35	0.4	V
V_F	$I_F=200\text{mA}$		0.42	0.5	V
C_T	$V_R=4.0\text{V}, f=1.0\text{MHz}$		8.5	10	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		4.0	5.0	ns

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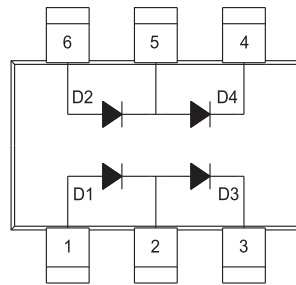
SOT 26 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

PIN CONFIGURATION

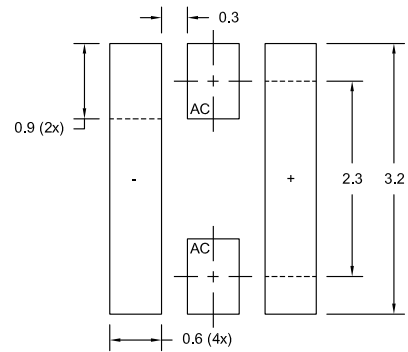


LEAD CODE:

- 1) Anode D1
- 2) Cathode D1, Anode D3
- 3) Cathode D3
- 4) Cathode D4
- 5) Anode D4, Cathode D2
- 6) Anode D2

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OPTIONAL MOUNTING PADS
For Bridge Rectifier Configuration
 (Dimensions in mm)



R2 (12-February 2010)